

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Yi Ding  
Assignee: Mosel Vitelic, Inc.  
Title: Nonvolatile Memory Cell With Multiple Floating Gates Formed After the Select Gate  
Application No.: Unassigned Filing Date: Filed Herewith  
Examiner: Unassigned Group Art Unit: Unassigned  
Docket No.: M-15171 US

San Jose, California  
July 29, 2003

Mail Stop Patent Application  
Commissioner For Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)**

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed.

Citation of these documents shall not be construed as:

1. an admission that the documents are necessarily prior art with respect to the instant invention;
2. a representation that a search has been made, other than as described above; or
3. an admission that the information cited herein is, or is considered to be material to patentability as defined in § 1.56(b).

No fee is believed to be required. If a fee is required for this Information Disclosure Statement, please charge the fee to Deposit Account No. 50-2257. This paper is being submitted in duplicate.

**EXPRESS MAIL LABEL NO.:**

**EE 508 123 018 US**

Respectfully submitted,

*Michael Shenker*

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Attorney for Applicant(s)  
Reg. No. 34,250

U.S. Department of Commerce, Patent and Trademark Office					Atty Docket No.		Serial No.	
					M-15171 US		Unassigned	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Applicant(s)			
(Use several sheets if necessary)					Yi Ding			
					Filing Date		Group	
					Filed Herewith		Unassigned	
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	5,402,371	28 Mar. 1995	Ono				
	AB	5,856,943	5 Jan. 1999	Jenq				
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	AD	6,130,129	10 Oct. 2000	Chen				
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	AP	Ma, Y.; Pang, C.S.; Pathak, J.; Tsao, S.C.; Chang, C.F.; Yamauchi, Y.; Yoshimi, M. "A Novel High Density Contactless Flash Memory Array Using Split-Gate Source-Side-Injection Cell for 5V-Only Applications," 1994 Symposium on VLSI Technology Digest of Technical Papers, pages 49-50.						
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Examiner			Date Considered					
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.</p>								

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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Examiner			Date Considered				
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